93120			
	IN THE UNITED STATES PATENT AND TRADEMARK OFFICE		

In Re U.S. Pate	nt Application)
Applicant:	Tetsuhiro IIDA et al.)
Serial No.:	To Be Assigned))
Filed:	Herewith))
For:	METHOD FOR PRODUCING SINGLE CRYSTAL SILICON, METHOD FOR PRODUCING SINGLE CRYSTAL SILICON WAFER, SEED CRYSTAL FOR PRODUCING SINGLE CRYSTAL SILICON, SINGLE CRYSTAL SILICON WAFER	,)))))))

INFORMATION DISCLOSURE STATEMENT

)

Commissioner for Patents P. O. Box 1450 Alexandria, VA 22313

Sir:

Pursuant to 37 C.F.R. §1.97, a list of documents is disclosed on the attached Form PTO-1449 that may be material to the examination of this application. The cited references are enclosed herewith.

Documents for which the supplied date of publication lists the year of publication without the month were published sufficiently earlier than the effective U.S. filing date and any foreign priority date, so that the particular month of publication is not in issue. Pursuant to §609 of the MPEP, it is understood that the month of publication is not required when the particular month of publication is not in issue.

No inferences should be drawn that the attached list represents a comprehensive investigation, or that any material disclosed is equivalent to the subject invention. In addition, none of the documents that have publication dates prior to the priority date of the above application anticipate the invention in this application.

Atty. Docket No.: 93120

Applicant also encloses a copy of the PCT Search Report and cited references therein.

The cited document(s) disclose numerous specific features. There has been no attempt to list each and every feature disclosed by each document. The Examiner is requested to review the document(s) and determine the extent of the materiality of the document disclosures with respect to the present invention.

The discussion of any art and the citation of any document(s) herein is not to be construed as an admission that the art or document disclosure is necessarily within the invention field of endeavor, that the art or document disclosure is necessarily prior in time to a particular date which may be relevant to the instant patent application, and/or that the art or document disclosure is otherwise necessarily prior art as defined by the patent law with respect to the instant invention and application.

Also, there is reserved the right to later set forth how the instant invention is distinguished over the disclosure of any document or other art, including the disclosures of the art and document(s) recited herein, that may be cited by the Examiner in rejecting a claim in the instant patent application. The recitation herein of the art and document(s) is not to be construed as an assertion that more pertinent art could not possibly be in existence.

Respectfully submitted,

Gerald T. Shekleton

Registration No. 27,466

gradat. Well

Dated: October 19, 2004

WELSH & KATZ, LTD.

120 South Riverside Plaza

22nd Floor

Chicago, Illinois 60606

Telephone: 312-655-1500

2

PTO/SB/08A & (04-03) Approved for use through 04/30/2003. OMB 0651-0031
U.S. Patent and Trademark Office: U.S. DEPARTMENT OF COMMERCE

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number Complete if Known
Unassigned Substitute for form 1449/PTO **Application Number** INFORMATION DISCLOSURE Filing Date October 19, 2004 STATEMENT BY APPLICANT **First Named Inventor** Tetsuhiro et al. Art Unit Unassigned (use as many sheets as necessary) **Examiner Name** Unassigned Sheet of 1 Attorney Docket Number 93120

U.S. PATENT DOCUMENTS						
Examin er Initials*	Cite No.1	Document Number Number-Kind Code ^{2 (il known)}	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines Where Relevant Passages or Relevant Figures Appear	
		4,002,523	01/11/1977	Dyer		
		5,911,823	06/15/1999	Sonoda et al.		
				P-4111-15, 11411-14		

	FOREIGN PATENT DOCUMENTS					
Cite No.1	Foreign Patent Document Country Code ³ -Number ⁴ -Kind Code ⁵ (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁶	
	JP 63123893	05/27/1988	Shoichi et al.		Abstract	
	JP 03080184	04/04/1991	NEC Corporation		Abstract	
	JP 57-017494	01/29/1982	Toshiba Corporation		Abstract	
	JP 09-165298	06/24/1997	Koji et al.		Abstract	
		Cite	Cite No.1 Foreign Patent Document Country Code ³ -Number ⁴ -Kind Code ³ (if known) Publication Date MM-DD-YYYY JP 63123893 05/27/1988 JP 03080184 04/04/1991 JP 57-017494 01/29/1982	Cite No.1 Foreign Patent Document Country Code ³ -Number ⁴ -Kind Code ³ (if known) Publication Date MM-DD-YYYY Name of Patentee or Applicant of Cited Document JP 63123893 05/27/1988 Shoichi et al. JP 03080184 04/04/1991 NEC Corporation JP 57-017494 01/29/1982 Toshiba Corporation	Cite No.1 Foreign Patent Document Country Code ³ -Number ⁴ -Kind Code ³ (ff known) Publication Date MM-DD-YYYY Name of Patentee or Applicant of Cited Document Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear JP 63123893 05/27/1988 Shoichi et al. JP 03080184 04/04/1991 NEC Corporation JP 57-017494 01/29/1982 Toshiba Corporation	

Examiner nitials*	Cite No.1	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	1 ₈
		Murthy et al.; "Growth of Dislocation-Free Silicon Crystals in the (110) Direction for Use as Neutron Monochromators," <i>Journal of Crystal Growth</i> , Vol. 52, (1981), pp. 391-395.	
		Hoshikawa et al.; "Dislocation-Free Czochralski Silicon Crystal Growth without the Dislocation-Elimination-Necking Process," <i>Japan Journal of Applied Phys.</i> , Vol. 38 (1999) pp. L1369-L1371.	

Examiner	Date	
Signature	Considered	

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹Applicant's unique citation designation number (optional). ²See Kind Codes of USPTO Patent Documents at www.uspto.gov or MPEP 901.04. ³Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶Applicant is to place a check mark here if English language Translation is attached.

Burden Hour Statement: This form is estimated to take 2.0 hours to complete. Time will vary depending upon the needs of the individual case. Any comments on the amount of time you are required to complete this form should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, Washington, DC 20231. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Assistant Commissioner for Patents, Washington, DC 20231.